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Front Matter: Volume 9748

, "Front Matter: Volume 9748," Proc. SPIE 9748, Gallium Nitride Materials and Devices XI, 974801 (18 July 2016); doi: 10.1117/12.2239452

SPIE.

Event: SPIE OPTO, 2016, San Francisco, California, United States

PROCEEDINGS OF SPIE

Gallium Nitride Materials and Devices XI

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Ulrich T. Schwarz
Jong-In Shim
Editors

15–18 February 2016
San Francisco, California, United States

Sponsored and Published by
SPIE

Volume 9748

Proceedings of SPIE 0277-786X, V. 9748

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Gallium Nitride Materials and Devices XI, edited by Jen-Inn Chyi, Hiroshi Fujioka, Hadis Morkoç,
Yasushi Nanishi, Ulrich T. Schwarz, Jong-In Shim, Proc. of SPIE Vol. 9748, 974801
© 2016 SPIE · CCC code: 0277-786X/16/\$18 · doi: 10.1117/12.2239452

Proc. of SPIE Vol. 9748 974801-1

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Author(s), "Title of Paper," in *Gallium Nitride Materials and Devices XI*, edited by Jen-Inn Chyi, Hiroshi Fujioka, Hadis Morkoç, Yasushi Nanishi, Ulrich T. Schwarz, Jong-In Shim, Proceedings of SPIE Vol. 9748 (SPIE, Bellingham, WA, 2016) Article CID Number.

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781628419832

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) • Fax +1 360 647 1445

SPIE.org

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Contents

vii	<i>Authors</i>
ix	<i>Conference Committee</i>

BN II

9748 05	Heteroepitaxial growth of cubic boron nitride films on diamond(001) substrates and their <i>n</i>-type doping (Invited Paper) [9748-4]
---------	---

GROWTH I

9748 09	HVPE-GaN growth on GaN-based advanced substrates by Smart Cut (Invited Paper) [9748-8]
---------	---

GROWTH II

9748 0K	Optical and crystal quality improvement in green emitting In_xGa_{1-x}N multi-quantum wells through optimization of MOCVD growth [9748-18]
---------	---

CHARACTERIZATION I

9748 0L	Quantum well intermixing and radiation effects in InGa_N/Ga_N multi quantum wells (Invited Paper) [9748-19]
---------	--

CHARACTERIZATION II

9748 0Q	New directions in GaN photonics (Invited Paper) [9748-24]
9748 0S	Analysis of radiative and non-radiative lifetimes in GaN using accurate internal-quantum-efficiency values estimated by simultaneous photoluminescence and photo-acoustic measurements [9748-27]

CHARACTERIZATION III

9748 0U	Approaches to highly efficient UV emitters based on AlGa_N quantum wells (Invited Paper) [9748-29]
9748 0W	Influence of vacancies on Ga_N/Al_N interface characteristics [9748-31]

ELECTRON DEVICES

- 9748 0Y **Interface control technologies for high-power GaN transistors: Self-stopping etching of p-GaN layers utilizing electrochemical reactions (Invited Paper)** [9748-33]
- 9748 0Z **Monolithic enhancement-mode and depletion-mode GaN-based MOSHEMTs (Invited Paper)** [9748-34]

LASERS I

- 9748 15 **Development for ultraviolet vertical cavity surface emitting lasers** [9748-40]

LASERS II

- 9748 17 **Continuous wave operation of high power GaN-based blue vertical-cavity surface-emitting lasers using epitaxial lateral overgrowth (Invited Paper)** [9748-42]
- 9748 18 **Optical-loss suppressed InGaN laser diodes using undoped thick waveguide structure (Invited Paper)** [9748-43]
- 9748 19 **AlGaInN laser diode technology for systems applications** [9748-44]
- 9748 1A **InGaN/GaN DFB laser diodes at 434 nm with deeply etched sidewall gratings** [9748-45]
- 9748 1B **Comparison of nonpolar III-nitride vertical-cavity surface-emitting lasers with tunnel junction and ITO intracavity contacts** [9748-46]

NANOSTRUCTURES

- 9748 1E **Linearly polarized single photons from small site-controlled GaN nanowire quantum dots** [9748-49]
- 9748 1G **Strain engineered high reflectivity DBRs in the deep UV** [9748-51]

LEDs I

- 9748 1J **Deep ultraviolet light-emitting and laser diodes (Invited Paper)** [9748-54]
- 9748 1O **Influence of the LED heterostructure on the degradation behavior of (InAlGa)N-based UV-B LEDs** [9748-59]

LEDs II

- 9748 1S **Tunable, full-color nanowire light emitting diode arrays monolithically integrated on Si and sapphire** [9748-63]

LEDS III

- 9748 1U **High-efficiency blue LEDs with thin AlGaIn interlayers in InGaIn/GaN MQWs grown on Si (111) substrates (Invited Paper)** [9748-65]
- 9748 1V **GaN-based superluminescent diodes with long lifetime** [9748-66]
- 9748 1W **Determination of internal quantum efficiency in GaN by simultaneous measurements of photoluminescence and photo-acoustic signals** [9748-67]
- 9748 1Z **Designing optically pumped InGaIn quantum wells with long wavelength emission for a phosphor-free device with polarized white-light emission** [9748-71]
- 9748 20 **Hierarchical growth of GaN nanowires for light emitting diode applications** [9748-72]

POSTER SESSION

- 9748 25 **Enhancement of indium incorporation to InGaIn MQWs on AlIn/GaN periodic multilayers** [9748-78]
- 9748 26 **Exciton localization in (11-22)-oriented semi-polar InGaIn multiple quantum wells** [9748-79]
- 9748 27 **Wurtzite/zinc-blende electronic-band alignment in basal-plane stacking faults in semi-polar GaN** [9748-80]
- 9748 28 **Optical investigation of microscopic defect distribution in semi-polar (1-101 and 11-22) InGaIn light-emitting diodes** [9748-81]

Authors

Numbers in the index correspond to the last two digits of the six-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first four digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Akazawa, Masamichi, 0Y	Hagino, Hiroyuki, 18
Alves, E., 0L	Hamaguchi, Tatsushi, 17
Alves, L. C., 0L	Han, Jung, 0Q
Amilusik, Mikolaj, 09	Hashizume, Tamotsu, 0Y
Andrade, Nicolas, 28	Hernandez-Balderama, L., 1G
Arakawa, Yasuhiko, 1E	Hoffmann, M. P., 1G
Arif, Ronald A., 0K	Holmes, Mark J., 1E
Arita, Munetaka, 1E	Ichikawa, Shuhei, 0U
Armour, Eric A., 0K	Imafuji, Osamu, 18
Asif, Fatima, 1J	Ito, Toshihide, 1U
Avrutin, Vitaliy, 25, 26, 27, 28	Iwinska, Malgorzata, 09
Ben Sedrine, N., 0L	Izumi, Shouichiro, 17
Berkman, Erkan A., 0K	Izyumskaya, Natalia, 25, 26, 27, 28
Bezyazychnaya, Tatyana V., 0W	Kabanau, Dzmitri M., 0W
Bobea, M., 1G	Kaess, F., 1G
Boćkowski, Michal, 09, 19	Kako, Satoshi, 1E
Bryan, I., 1G	Kao, Tsung-Ting, 15
Carlin, J.-F., 1V	Katayama, Takuma, 18
Castiglia, A., 1V	Kawaguchi, Masao, 18
Caulmilone, Raphael, 09	Kawakami, K., 0S, 1W
Chang, Jhe-Hao, 0Z	Kawakami, Yoichi, 0U
Choi, Kihyun, 1E	Kelly, Anthony E., 19, 1A
Cohen, D. A., 1B	Khan, Asif, 1J
Collazo, R., 1G	Kimura, Shigeya, 1U
Correia, M. R., 0L	Kirste, R., 1G
Czernecki, R., 19	Knauer, Arne, 1O
Das, Saikat, 25, 26, 27, 28	Kneissl, Michael, 1O
DenBaars, Steven P., 1B, 1Z	Kolbe, Tim, 1O
Detchprohm, Theeradetch, 15	Kowsz, Stacy J., 1Z
Docherty, Kevin E., 1A	Kucharski, R., 19
Duelk, M., 1V	Kueller, Viola, 1O
Dupuis, Russell D., 15	Kuhn, Christian, 1O
Edamoto, Masaaki, 0Y	Kumazaki, Yusuke, 0Y
Einfeldt, Sven, 1O	Lebiadok, Yahor V., 0W
Enslin, Johannes, 1O	Lee, Cheul-Ro, 20
Farrell, Robert M., 1Z	Lee, Ching-Ting, 0Z
Fijalkowski, Michal, 09	Lee, Soo Min, 0K
Franke, A., 1G	Leitão, M. P., 0L
Freitas, A., 0L	Leonard, J. T., 1B
Funato, Mitsuru, 0U	Leszczyński, M., 19
Fuutagawa, Noriyuki, 17	Litwin-Staszewska, Elzbieta, 09
Gerhold, M., 1G	Liu, Yuh-Shiuan, 15
Gil, Bernard, 26	Lobo Ploch, Neysha, 1O
Glaab, Johannes, 1O	Lorenz, K., 0L
Grandjean, N., 1V	Lourenço, M. B., 0L
Grzanka, Ewa, 09	Lucznik, Boleslaw, 09
Grzegory, Izabella, 09	Margalith, T., 1B
Guiot, Eric, 09	Marona, L., 19
Hafiz, Shopan, 25, 27, 28	Matuschek, N., 1V

Mehnke, Frank, 1O
 Mehta, Karan, 15
 Meredith, Wyn, 1A
 Mi, Zetian, 1S
 Monavarian, Morteza, 25, 26, 27, 28
 Monteiro, T., 0L
 Morkoç, Hadis, 25, 26, 27, 28
 Mrotzek, Tobias, 09
 Muhtadi, Sakib, 1J
 Murayama, Masahiro, 17
 Najda, S. P., 19
 Nakamura, Shuji, 1B, 1Z
 Nakano, T., 0S, 1W
 Narui, Hironobu, 17
 Navamathavan, R., 20
 Ng, T. K., 1B
 Nguyen, Hieu P. T., 1S
 Nowakowska-Siwinska, Anna, 09
 Nozaki, Shinichiro, 18
 Nunoue, Shinya, 1U
 Obheroi, Sonika, 20
 Odedina, Opeoluwa, 1A
 Okada, Aoi, 1U
 Ooi, B. S., 1B
 Özgür, Ümit, 25, 26, 27, 28
 Papasouliotis, George D., 0K
 Park, Sunghyun, 0Q
 Peres, M., 0L
 Perlín, P., 19
 Ponce, Fernando A., 15
 Pynn, Christopher D., 1Z
 Ra, Yong-Ho, 1S
 Ra, Yong-Ho, 20
 Raj, Rishabh, 20
 Ramos, Frank, 0K
 Rass, Jens, 1O
 Redondo-Cubero, A., 0L
 Rezzonico, R., 1V
 Rodrigues, J., 0L
 Rosales, Daniel, 26
 Rossetti, M., 1V
 Ryabtsev, Gennadii I., 0W
 Sato, Taketomo, 0Y
 Seiss, Martin, 09
 Sequeira, M. C., 0L
 Shen, C., 1B
 Shen, Shyh-Chiang, 15
 Shih, Ishiang, 1S
 Sitar, Z., 1G
 Slight, Thomas J., 1A
 Sochacki, Tomasz, 09
 Speck, James S., 1B, 1Z
 Stoelmacker, Christoph, 1O
 Suski, T., 19
 Takigawa, Shinichi, 18
 Tanaka, Tsuyoshi, 18
 Targowski, G., 19
 Tseng, Chun-Yen, 0Z
 Tucker, Eric, 0K
 Tweedie, J., 1G
 Uesugi, Kenjiro, 1U
 Vélez, C., 1V
 Wang, Renjie, 1S
 Washiyama, S., 1G
 Watson, S., 19
 Wernicke, Tim, 1O
 Weyers, Markus, 1O
 Wisniewski, P., 19
 Wu, Feng, 1Z
 Wu, Yuanpeng, 1S
 Xie, Hongen, 1S
 Xiong, Kanglin, 0Q
 Yamaguchi, A. A., 0S, 1W
 Yin, Hong, 05
 Yoder, P. Douglas, 15
 Yonkee, B. P., 1B
 Yoshida, Hisashi, 1U
 Young, E. C., 1B
 Yuan, Ge, 0Q
 Zhang, Cheng, 0Q
 Zhang, Fan, 28
 Zhao, Songrui, 1S
 Zhuravlev, Konstantin S., 0W

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- 1 BN I
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- 4 Growth II
Michał Bockowski, Institute of High Pressure Physics (Poland)
- 5 Characterization I
Hiroshi Fujioka, The University of Tokyo (Japan)
- 6 Characterization II
Frank Bertram, Otto-von-Guericke- Universität Magdeburg (Germany)
- 7 Characterization III
Robert Martin, University of Strathclyde (United Kingdom)
- 8 Electron Devices
Jen-Inn Chyi, National Central University (Taiwan)
- 9 Lasers I
Ulrich T. Schwarz, Technische Universität Chemnitz (Germany)
- 10 Lasers II
Hideki Hirayama, RIKEN (Japan)
- 11 Nanostructures
Elison Matioli, Ecole Polytechnique Fédérale de Lausanne (Switzerland)
- 12 LEDs I
Jong-In Shim, Hanyang University (Korea, Republic of)

- 13 LEDs II
Asif M. Khan, University of South Carolina (United States)
- 14 LEDs III
Hadis Morkoç, Virginia Commonwealth University (United States)